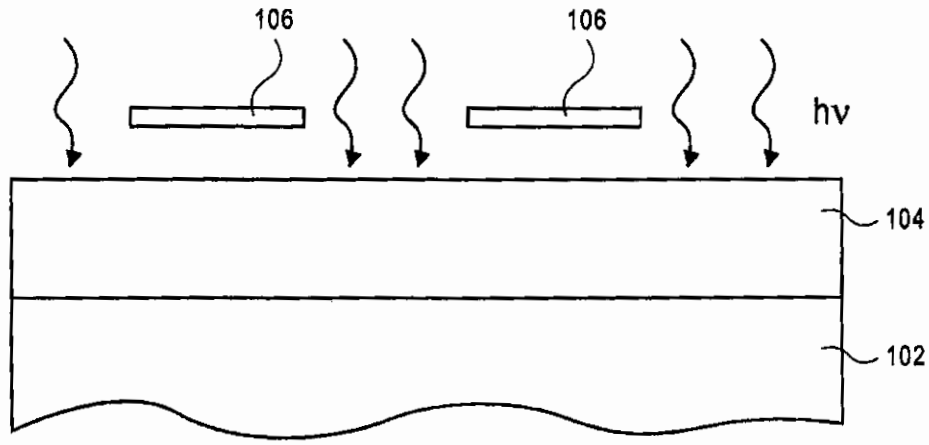


FIG. 1A
(PRIOR ART)

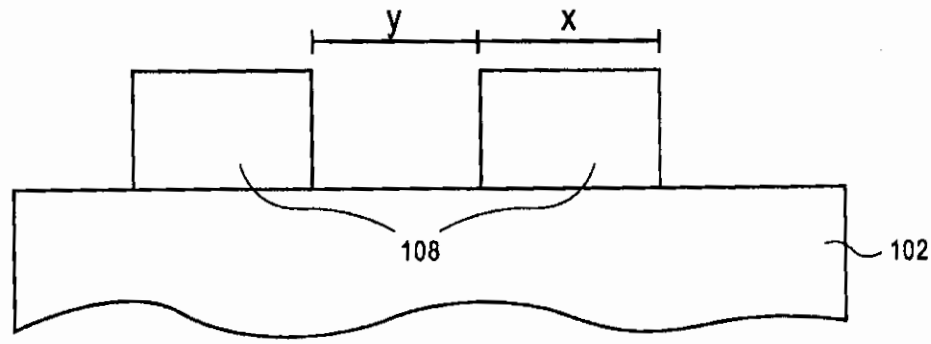


FIG. 1B
(PRIOR ART)

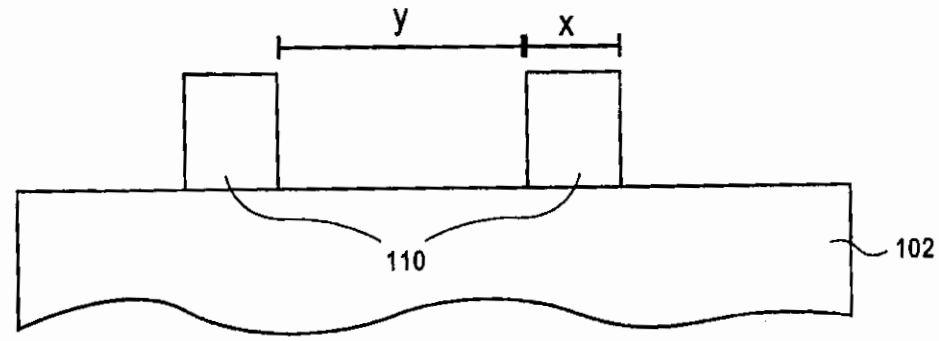


FIG. 1C
(PRIOR ART)

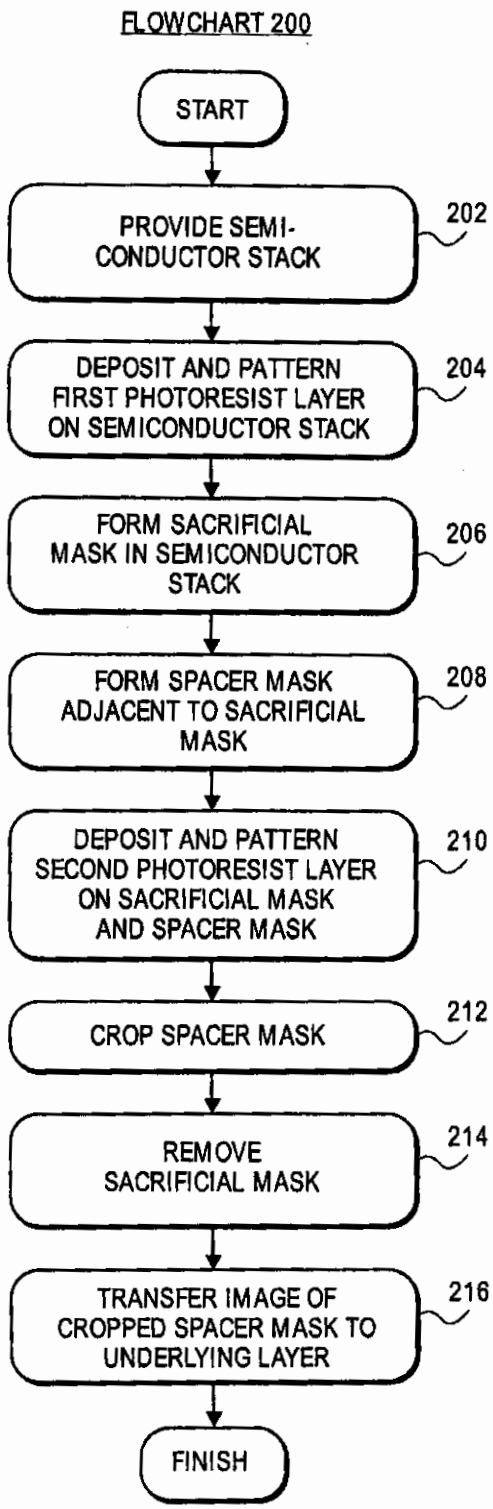

FLOWCHART 200
START
PROVIDE SEMI-CONDUCTOR STACK
202
DEPOSIT AND PATTERN FIRST PHOTORESIST LAYER ON SEMICONDUCTOR STACK
204
FORM SACRIFICIAL MASK IN SEMICONDUCTOR STACK
206
FORM SPACER MASK ADJACENT TO SACRIFICIAL MASK
208
DEPOSIT AND PATTERN SECOND PHOTORESIST LAYER ON SACRIFICIAL MASK AND SPACER MASK
210
CROP SPACER MASK
212
REMOVE SACRIFICIAL MASK
214
TRANSFER IMAGE OF CROPPED SPACER MASK TO UNDERLYING LAYER
216
FINISH

FIG. 2

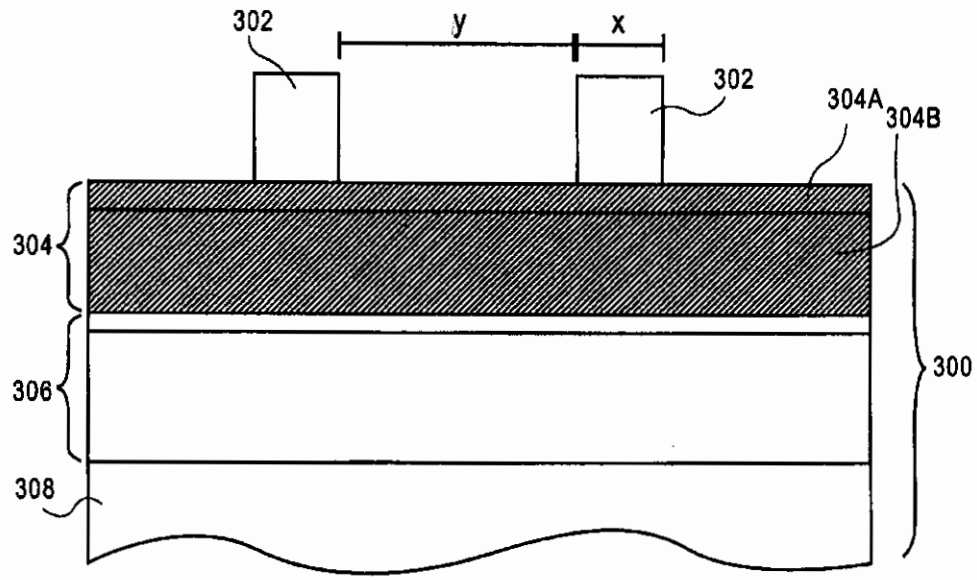

302
y
x
302
304A
304B
304
306
308
300

FIG. 3A

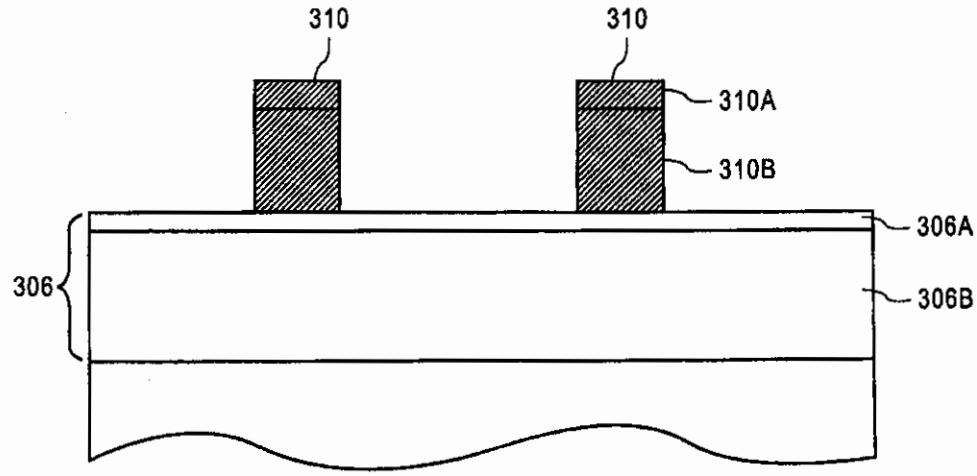

310
310
310A
310B
306A
306
306B

FIG. 3B

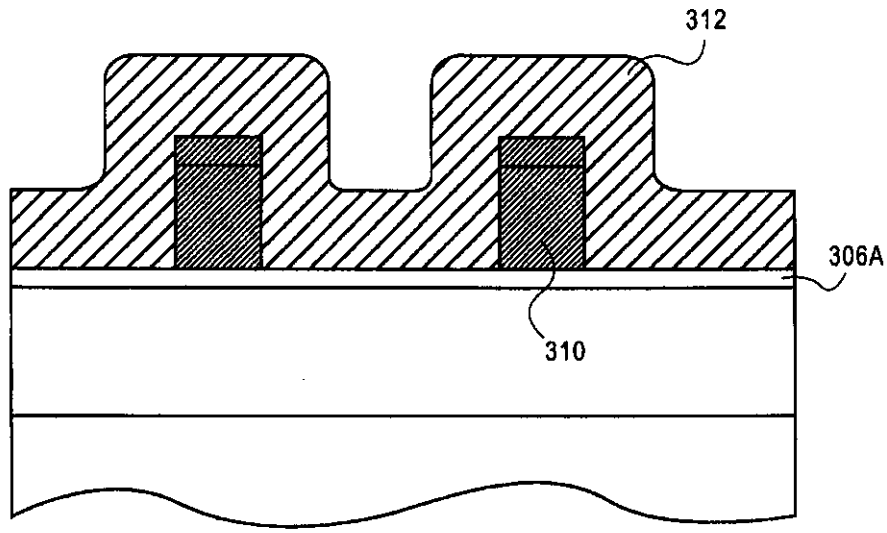


FIG. 3C

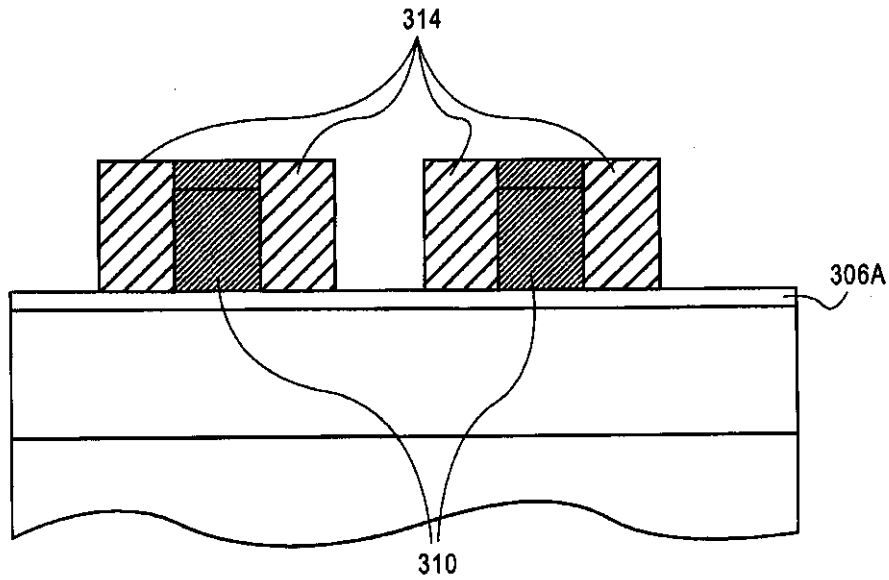


FIG. 3D

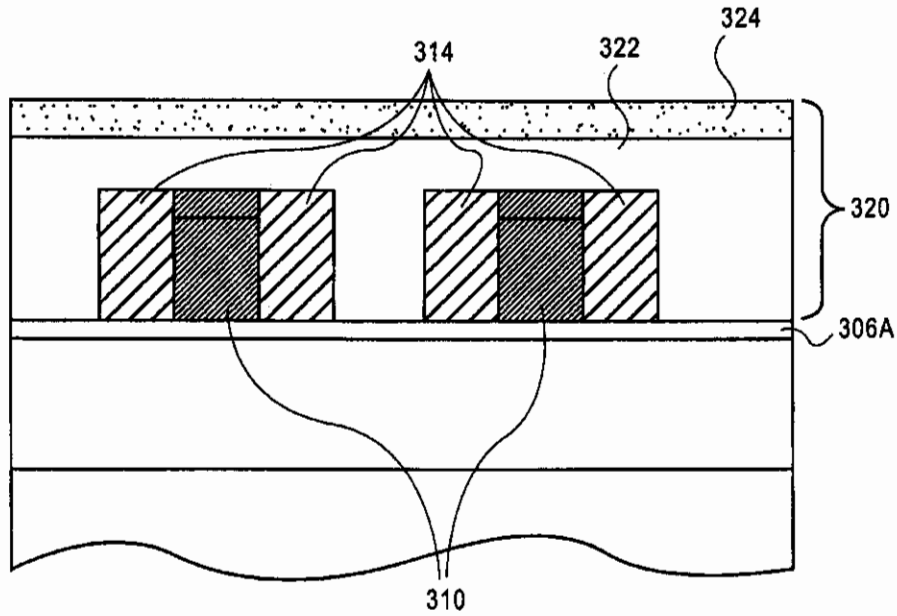


FIG. 3E

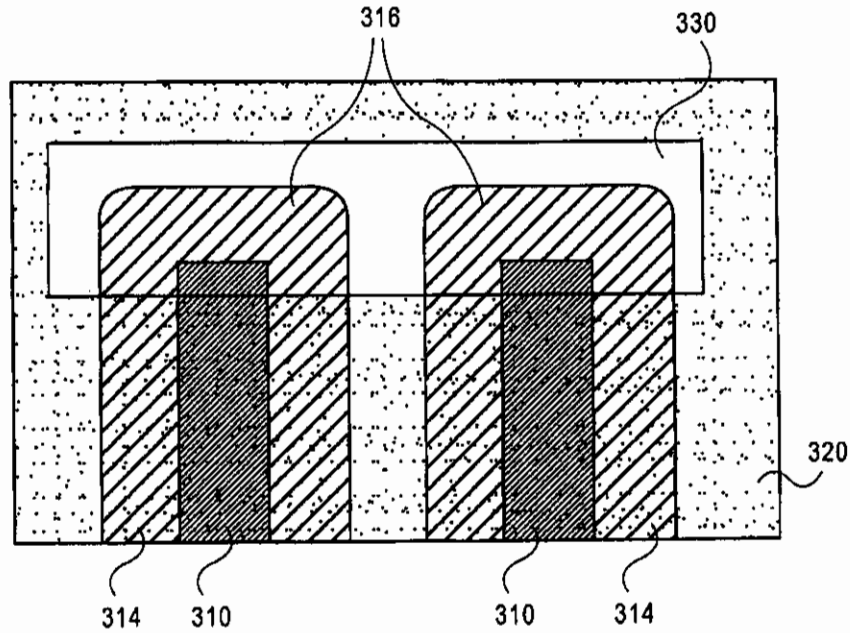


FIG. 3E'

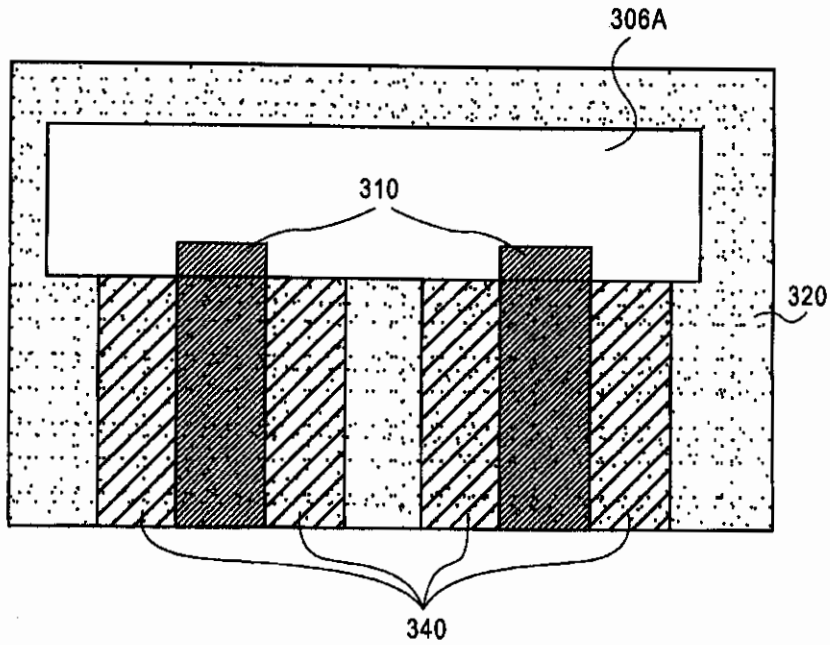


FIG. 3F

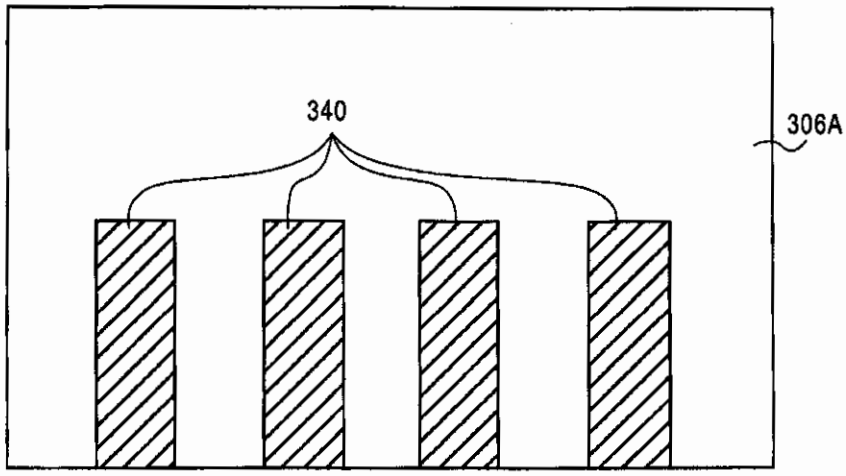


FIG. 3G

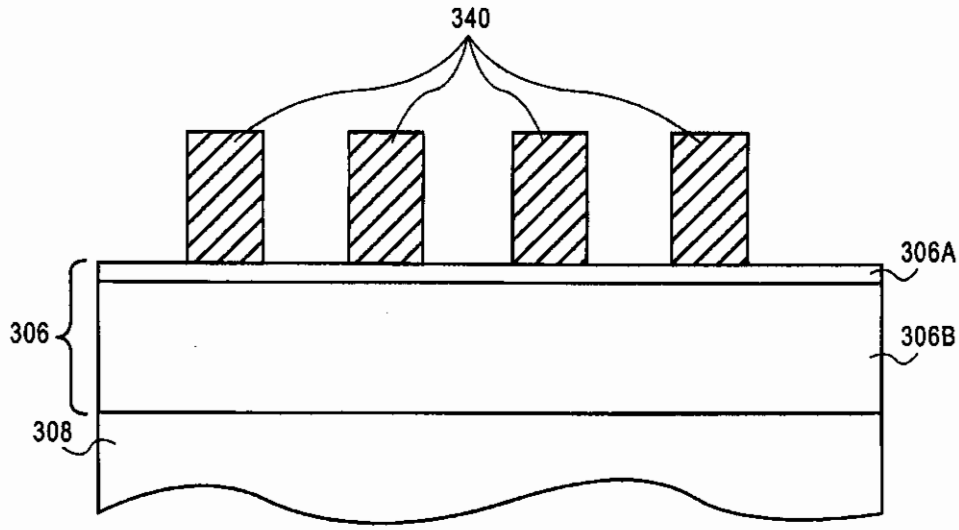


FIG. 3G'

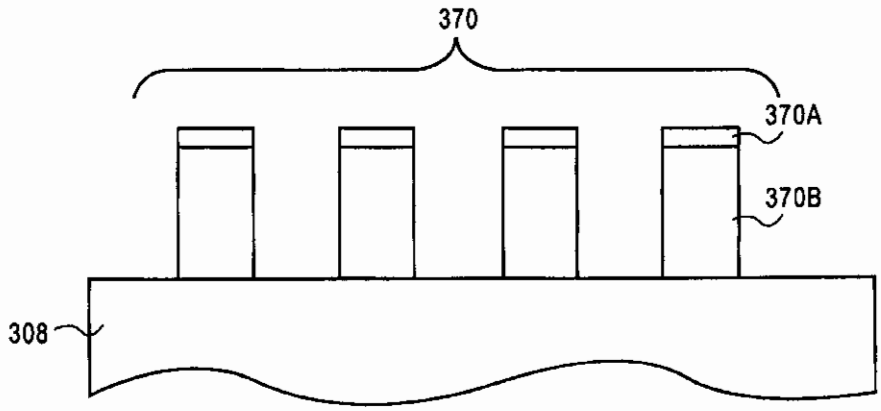


FIG. 3H

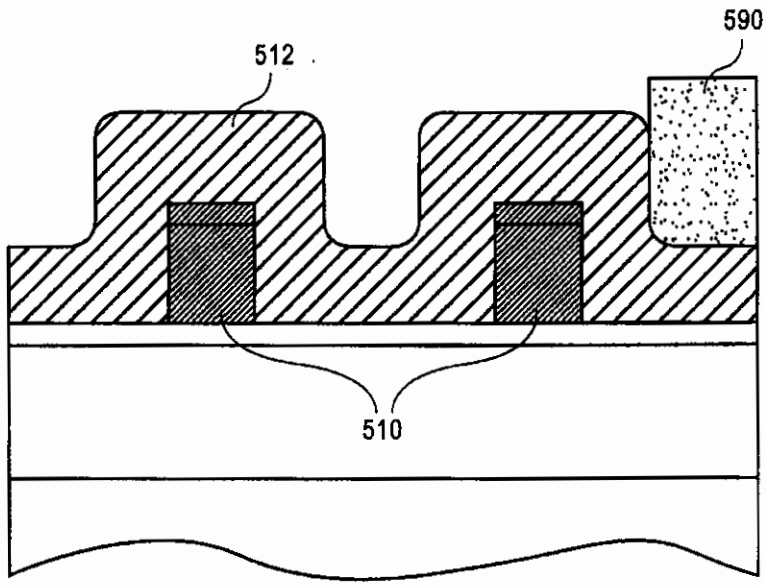


FIG. 5A

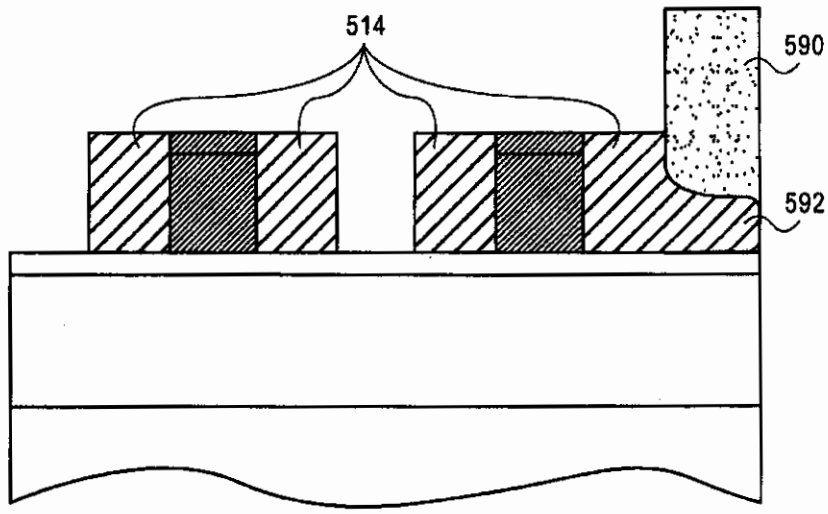


FIG. 5B

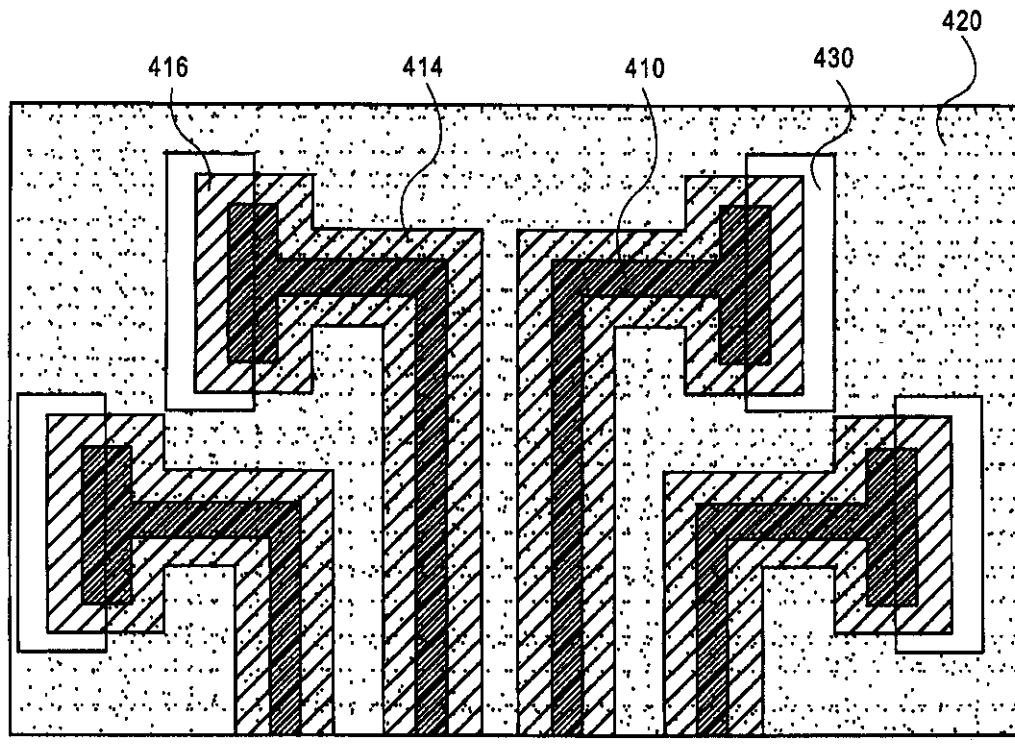


FIG. 4A

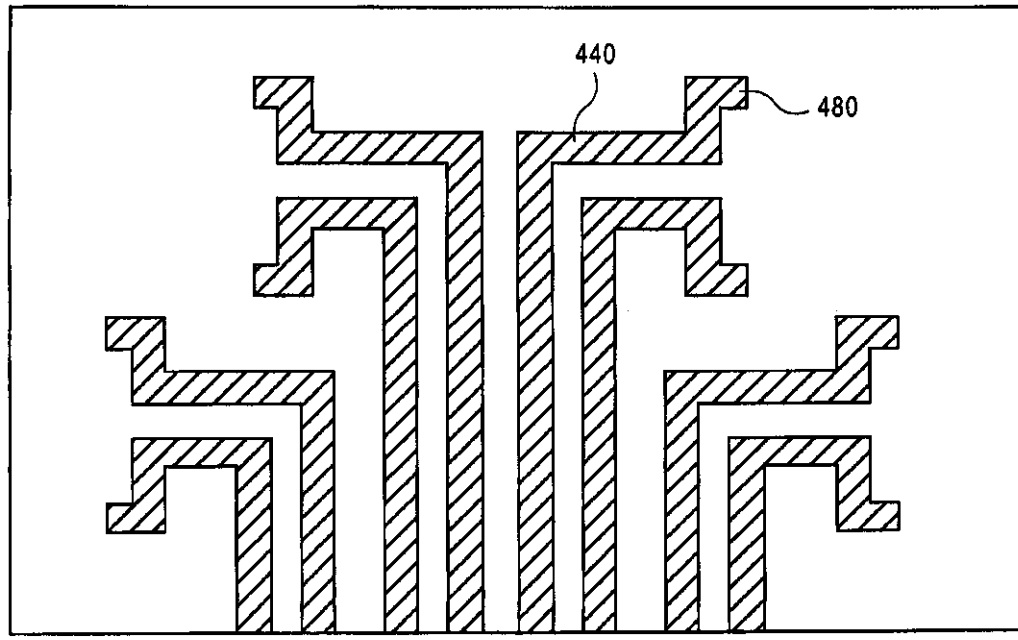


FIG. 4B

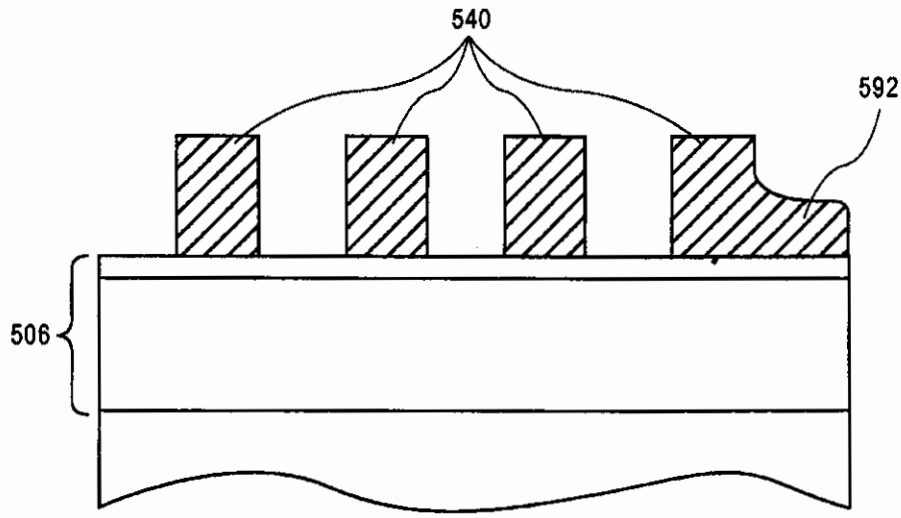


FIG. 5C

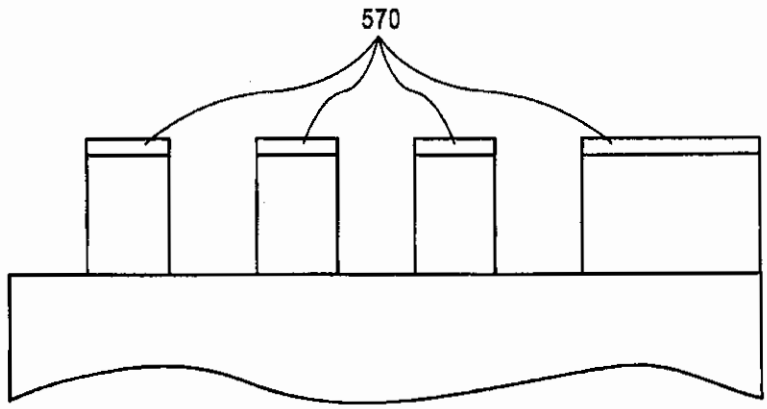


FIG. 5D

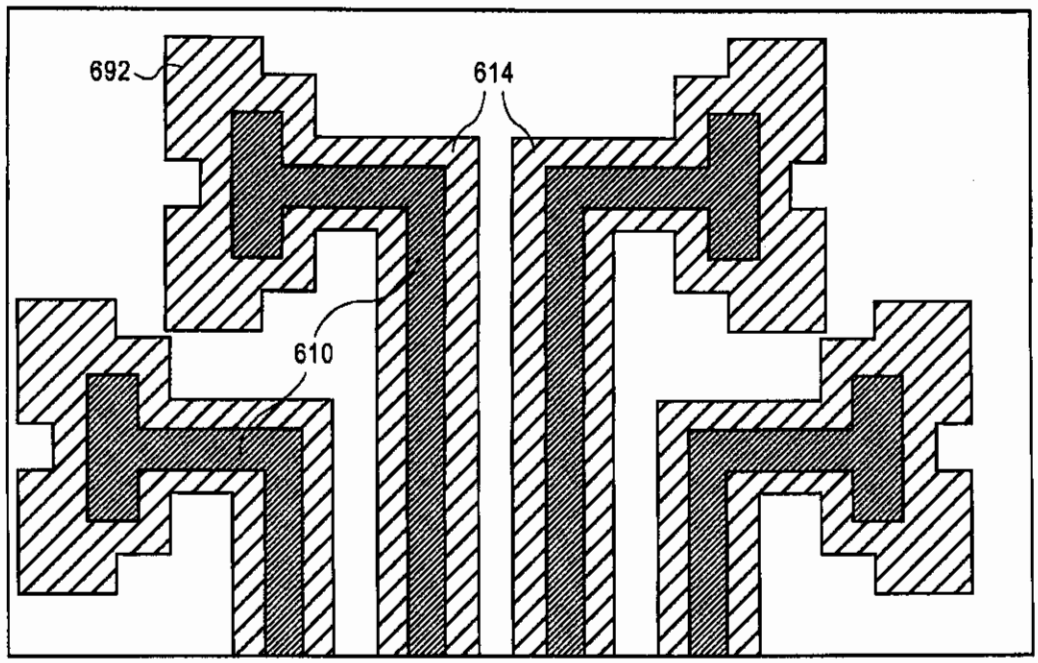


FIG. 6A

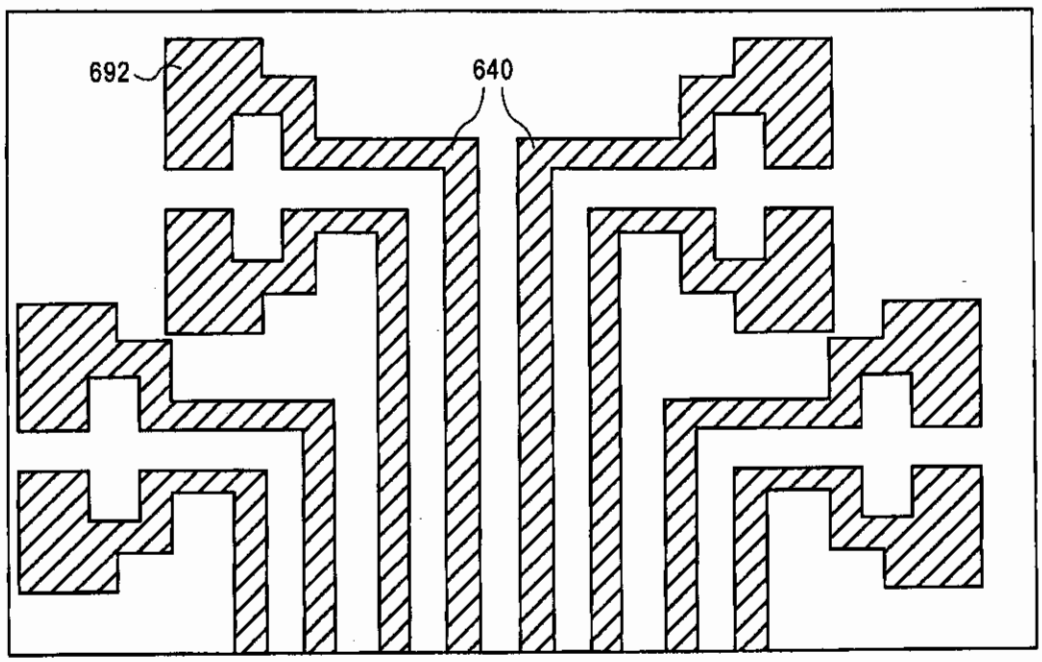


FIG. 6B